Notice of References Cited

Application/Control No. 10/736,859	Applicant(s)/Patent Under Reexamination YAO, JIE	
Examiner	Art Unit	
Fugene Lee	2815	Page 1 of 2

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	Α	US-6,492,704 B1	12-2002	Coroy, Trenton G.	257/461
	В	US-5,073,809	12-1991	Bigan et al.	257/458
	С	US-4,069,492	01-1978	Pankove et al.	257/79
	D	US-4,904,859	02-1990	Goossen et al.	250/214R
	E	US-5,818,096 A	10-1998	Ishibashi et al.	257/458
	F	US-US00RE38582E1	09-2004	White	257/448
	G	US-4137543	01-1979	Beneking, Heinz	257/184
	Н	US-5,144,406 A	09-1992	Hemings et al.	257/656
	1	US-6,265,727 B1	07-2001	Kozodoy et al.	257/21
	J	US-4,217,598	08-1980	d'Auria et al.	257/85
	К	US-5,621,238 A	04-1997	Dodd et al.	257/440
	L	US-4,527,179	07-1985	Yamazaki, Shunpei	257/13
	М	US-5,256,887 A	10-1993	Yang, Liyou	257/53

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	:				
	0					
	Р		·			
	Q					
	R					
	s					
	Т					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Ultrafast, dual-depletion region, InGaAs/InP p-i-n detector□□Effenberger, F.J.; Joshi, A.M.;□□Lightwave Technology, Journal of□□Volume 14, Issue 8, Aug. 1996 Page(s):1859 - 1864 □□
	٧	Metamorphic graded bandgap InGaAs-InGaAlAs-InAlAs double heterojunction p-i-l-n photodiodes□□Jae-Hyung Jang; Cueva, G.; Hoke, W.E.; Lemonias, P.J.; Fay, P.; Adesida, I.;□□Lightwave Technology, Journal of□□Volume 20, Issue 3, March 2002 Page(s):507 - 514
	w	InGaAsPN/InP based photodetectors for long wavelength (λ>1.65 μm) applications□□Wei, J.; Gokhale, M.R.; Thomson, J.; Forrest, S.R.;□□Lasers and Electro-Optics Society 1999 12th Annual Meeting. LEOS '99. IEEE□□Volume 2, 8-11 Nov. 1999 Page(s):742 - 743
	х	High-frequency InP/InGaAs pin photodiodes with efficient response at short wavelengths Diadiuk, V.; Alexander, S.B.; Groves, S.H.; Spears, D.L.; Indium Phosphide and Related Materials, 1991., Third International Conference.

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	Α	US-4,987,460	01-1991	Takasu et al.	257/103
	В	US-4,581,476	04-1986	Yamazaki, Shunpei	136/258
	С	US-4,784,702	11-1988	Henri, Yves	136/258
	D	US-5,329,150 A	07-1994	Schubert et al.	257/458
	Ε	US-			
	F	US-			
	G	US-			
	Н	US-			
	1	US-			
	J	US-			
	К	US-			
	L	US-			
	М	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	0					
	Ρ				·	
	ø					
	R.					
	s					
	Τ					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	
	٧	
	w	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.